

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD1348

DESCRIPTION

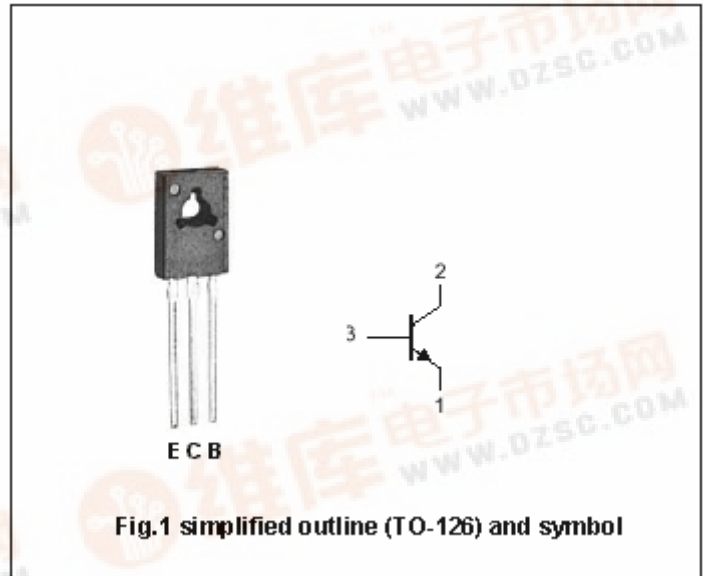
- With TO-126 package
- Complement to type 2SB986
- High current capacity

APPLICATIONS

- Power supplies, relay drivers, lamp drivers, electrical equipment

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	60	V
V _{CEO}	Collector-emitter voltage	Open base	50	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		4	A
I _{CM}	Collector current-peak		6	A
P _D	Total power dissipation	T _a =25°C	1.2	W
		T _c =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1.0mA ; R _{BE} =∞	50			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10 μ A ; I _C =0	6			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10 μ A ; I _E =0	60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.0A ; I _B =0.1A			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2.0A ; I _B =0.1A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =40V ; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =4V ; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =100mA ; V _{CE} =2V	100		560	
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =2V	40			
f _T	Transition frequency	I _C =50mA ; V _{CE} =10V		150		MHz
C _{OB}	Collector output capacitance	f=1MHz ; V _{CB} =10V		25		pF

◆ h_{FE-1} Classifications

R	S	T	U
100-200	140-280	200-400	280-560

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PACKAGE OUTLINE

